



深圳成光兴光电技术股份有限公司

SHENZHEN CGX OPTOELECTRONIC TECHNOLOGY, INC..

样品规格承认书

SAMPLE APPROVAL SHEET

客户名称

Company Name : _____

产品型号

Part Number: CPD-85H1C

送样日期

Sample Date: _____

APPROVED SIGNATURES (供应商确认)		
核准	品保	工程

客户确认：☐样品承认 ☐不予承认需重新送样 ☐不予承认不需送样

客户建议：_____

APPROVED SIGNATURES (客户确认)		
核准	工程	品保

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SIDE LOOK PHOTO DIODE

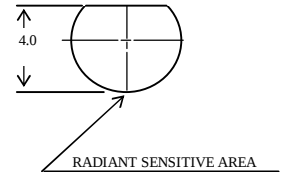
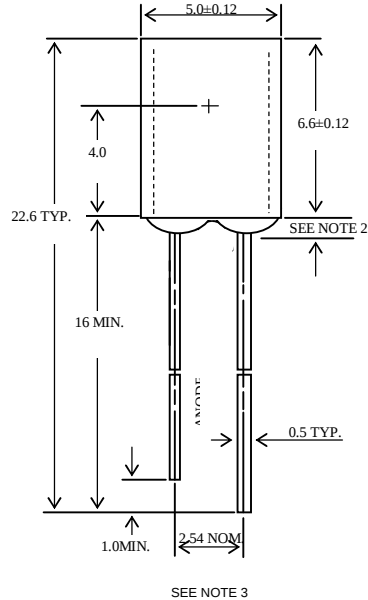
PART NO. : CPD-85H1C

Description

The CPD-85H1C is a photodiode mounted in special dark plastic package and suitable for the IRED (850nm/880nm/940nm) Type.

Package Dimensions

Unit: mm



Features

- High photo sensitivity
- Low junction capacitance
- High cut-off frequency
- Fast switching time

P ————>|———— N

Notes :

1. Tolerance is ± 0.25 mm unless otherwise noted.
2. Protruded resin under flange is 1.0 mm max.
3. Lead spacing is measured where the leads emerge from the package.

Absolute Maximum Ratings

@ $T_A=25^\circ\text{C}$

Parameter	Maximum Rating	Unit
Power Dissipation	150	mW
Operating Temperature Range	-25°C to $+85^\circ\text{C}$	
Storage Temperature Range	-40°C to $+100^\circ\text{C}$	
Lead Soldering Temperature	260°C for 5 seconds	



Optical-Electrical Characteristics

@ T_A=25°C

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Unit
Reverse Break Down Voltage	I _R =0.1mA Ee=0	V _(BR) R	30	-----	-----	V
Reverse Dark Current	V _R =10V Ee=0	I _D	-----	-----	30	nA
Open Circuit Voltage	λp= 850nm Ee=0.1mW/cm ²	V _{OC}	-----	350	-----	mV
Rise Time	V _R =10V λp=850nm	Tr	-----	30	-----	nsec
Fall Time	R _L =1KW	Tf	-----	30	-----	
Light Current	V _R =5V, λp=850nm Ee= 1mW/cm ²	I _L	9.5	20	-----	uA
Total Capacitance	V _R =3V, f=1MHz Ee=0	C _T	-----	25	-----	pF

Typical Optical-Electrical Characteristic Curves

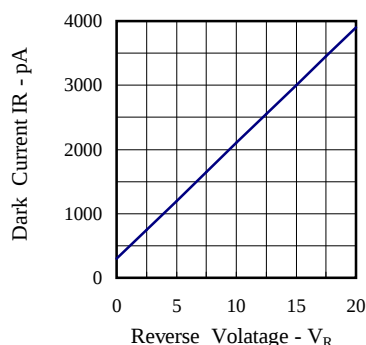


FIG.1 DARK CURRENT VS REVERSE VOLTAGE
T_{AMB}=25-°C, Ee=0 mW/cm²

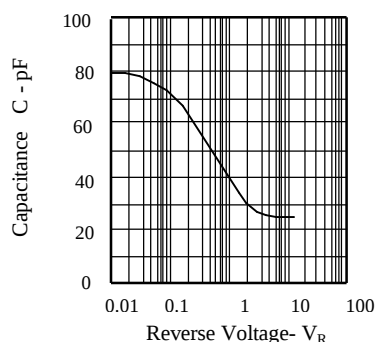


FIG.2 CAPACITANCE VS. REVERSE VOLTAGE
F=1MHz ; Ee=0mW/cm²

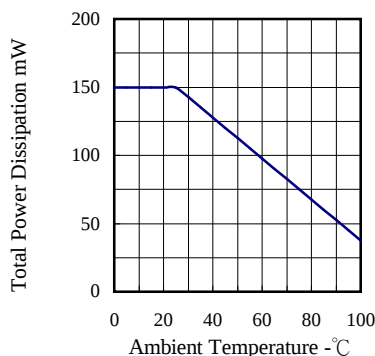


FIG.3 TOTAL POWER DISSIPATION
VS. AMBIENT TEMPERATURE

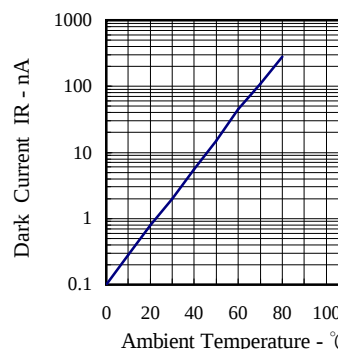


FIG.4 DARK CURRENT VS AMBIENT TEMPERATURE
V_R=10V, Ee=0 mw/cm²



Typical Optical-Electrical Characteristic Curves

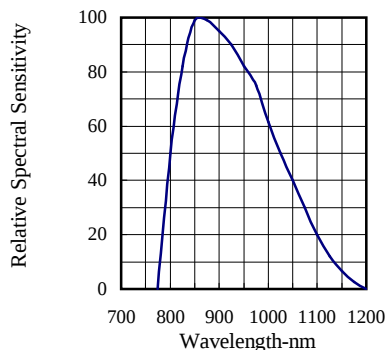


FIG.5 RELATIVE SPECTRAL SENSITIVITY
VS. WAVELENGTH

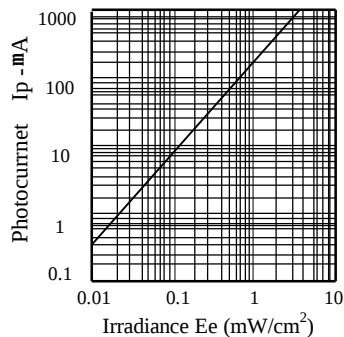


FIG.6 PHOTOCURRENT VS.
IRRADIANCE = 850 nm

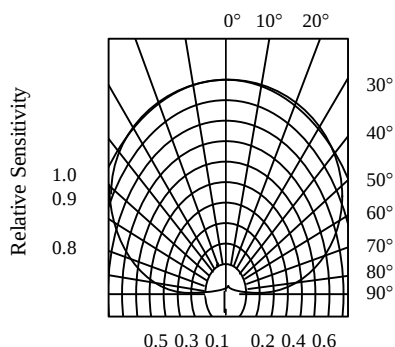


FIG.7 SENSITIVITY DIAGRAM



Reliability test items and test conditions

The reliability of products shall be satisfied with items listed below.

Confidence level : 90%

LTPD (group of permitted defect rate): 10%

No.	Item	Test Conditions	Test Hours/ Cycles	Sample Sizes	Ac/Re	Reference Standard
1	REFLOW Soldering	Temp. : 260 ±5	5secs	22PCS	0/1	JEITA ED-4701 300 302
2	Temperature Cycle	H : +100 15min ~ 5 min L : -40 15min	100Cycles	22PCS	0/1	JEITA ED-4701 100 305
3	Thermal Shock	H : +100 5min ~ 10 sec L : -10 5min	100Cycles	22PCS	0/1	MIL-STD-202G
4	High Temperature Storage	Temp. : 100	1000Hrs	22PCS	0/1	JEITA ED-4701 200 201
5	Low Temperature Storage	Temp. : -40	1000Hrs	22PCS	0/1	JEITA ED-4701 200 202
6	DC Operating Life	IF = 50 mA	1000Hrs	22PCS	0/1	Tested with CGX standard
7	High Temperature/ High Humidity	85 /RH85%	1000Hrs	22PCS	0/1	JEITA ED-4701 100 103

Notes : Failure Judgement Criteria : $IR \geq U \times 2$ $I_e \leq L \times 0.8$ $VF \geq U \times 1.2$

U : Upper Specification Limit L : Lower Specification Limit